

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
17 December 2009 (17.12.2009)

(10) International Publication Number
WO 2009/150561 A1

(51) International Patent Classification:
H01L 33/00 (2010.01)

High Tech Campus Building 44, NL-5656 AE Eindhoven (NL).

(21) International Application Number:
PCT/IB2009/052264

(74) Agents: BEKKERS, Joost, J., J. et al.; High Tech Campus Building 44, NL-5656 AE Eindhoven (NL).

(22) International Filing Date:
29 May 2009 (29.05.2009)

(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
08157943.5 10 June 2008 (10.06.2008) EP

(71) Applicant (for all designated States except DE, US):
KONINKLIJKE PHILIPS ELECTRONICS N.V. [NL/NL]; Groenewoudseweg 1, NL-5621 BA Eindhoven (NL).

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

(71) Applicant (for DE only): **PHILIPS INTELLECTUAL PROPERTY & STANDARDS GMBH** [DE/DE]; Lübeckertordamm 5, 20099 Hamburg (DE).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **VAN SPRANG, Hendrik, A** [NL/NL]; c/o High Tech Campus Building 44, NL-5656 AE Eindhoven (NL). **JAGT, Hendrik, J., B.** [NL/NL]; c/o High Tech Campus Building 44, NL-5656 AE Eindhoven (NL). **HUNSCHE, Berno** [DE/DE]; c/o High Tech Campus Building 44, NL-5656 AE Eindhoven (NL). **DIEDERICH, Thomas** [DE/DE]; c/o

Published:

— with international search report (Art. 21(3))

(54) Title: LED MODULE

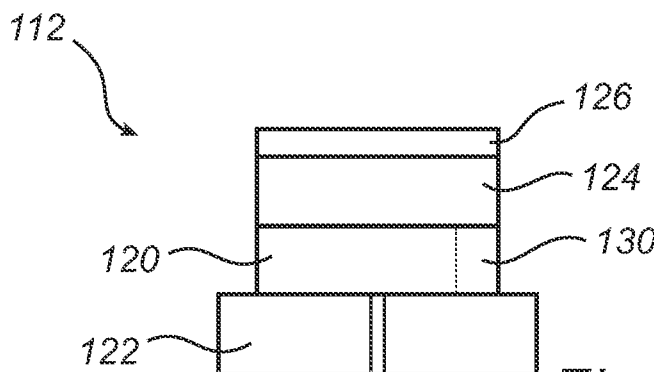


Fig. 4

(57) Abstract: The present invention relates to a LED module which converts pump light from a LED chip (120) to light at another wavelength, which is emitted from the module. The conversion takes place in a portion of a luminescent material (124). The color purity of the LED module is enhanced by reducing any leakage of pump light using a reflector in combination with an absorber. In one embodiment, the absorber is integrated as one or several thin absorbing layers between the layers of a multi-layer reflection filter (126); this may yield an even higher reduction of pump light leakage from the module.



WO 2009/150561 A1

LED module

FIELD OF THE INVENTION

The present invention relates to a lightsource, comprising a LED chip adapted for emitting excitation light in a first wavelength range; a wavelength converter adapted for converting excitation light to converted light in a second wavelength range; and a reflector, adapted for transmitting converted light, and for reflecting excitation light onto the wavelength converter.

BACKGROUND OF THE INVENTION

US 7,245,072 B2 discloses a LED module comprising a LED, a layer of a phosphor material, and a birefringent polymeric multi-layer reflection filter. The phosphor material, which is located between the reflection filter and the LED, emits visible light when illuminated with ultraviolet (UV) excitation light by the LED, and the filter serves for removing remaining, unconverted UV light from the optical output of the LED module. By using birefringent polymers in the reflector layer, better filtering of UV light having an oblique angle of incidence onto the filter is reported.

The use of multiple birefringent layers in the reflector however leads to complicated devices and/or fabrication methods.

SUMMARY OF THE INVENTION

It is an object of the present invention to provide a less complicated technique for removing excitation light from the light output of a LED module. To this end, there is provided a lightsource, comprising a LED chip adapted for emitting excitation light in a first wavelength range; a wavelength converter adapted for converting excitation light to converted light in a second wavelength range; a reflector, adapted for transmitting converted light, and for reflecting excitation light onto the wavelength converter; and an absorption layer, arranged for absorbing unconverted excitation light. The absorption layer assists in decreasing the amount of emitted excitation light.

Preferably, the reflector is a multi-layer reflector comprising a plurality of alternating layers of at least two different materials having at least two different indices of

refraction. Such reflectors may be given a high wavelength selectivity at a substantially normal angle of incidence of the light.

Preferably, the absorption layer is located between layers of the reflector. This configuration may even further reduce the amount of transmitted excitation light impinging on the reflector at an angle of incidence that deviates from the reflection filter's surface normal, and/or reduce the required number of process steps in the fabrication of an efficient filter. More preferably, at least one fourth of the total number of reflector layers is located on each side of the absorber.

Preferably, the wavelength converter is located between the reflector and the LED chip, as this configuration is beneficial from a conversion efficiency point of view. Preferably, the reflector, the absorption layer, the wavelength converter and the LED chip are joined to form a single device. This is a very compact and efficient configuration that is inexpensive to fabricate.

Preferably, the multi-layer reflector and the absorber have a total thickness of less than 2000 nm.

BRIEF DESCRIPTION OF THE DRAWINGS

This and other aspects of the present invention will now be described in more detail, with reference to the appended drawings showing a currently preferred embodiment of the invention.

Fig. 1 is a schematic sectional view of a LED module comprising a LED chip, a luminescent converter, a reflector and an absorber.

Fig. 2 is a schematic sectional view of the LED and the luminescent converter in fig. 1.

Fig. 3 is a schematic sectional view of a LED module having the luminescent converter, reflector, and absorber integrated with the LED chip.

Fig. 4 is a schematic sectional view of the LED in fig. 3.

Fig. 5 is a graph, illustrating the transmittance of a multi-layer reflector.

Fig. 6 is a graph, illustrating the transmittance of a multi-layer reflector comprising an absorber layer.

Fig. 7 is a schematic sectional view of a LED module, showing an alternative geometric configuration of the luminescent converter and the reflector.

Fig. 8 is a schematic sectional view of the LED, the luminescent converter, and the reflector in fig. 7.

Fig. 9 is a schematic sectional view of a LED module, showing yet another alternative geometric configuration of the luminescent converter and the reflector.

Fig. 10 is a schematic sectional view of the LED and the reflector in fig. 9.

Fig. 11 is a schematic sectional view of a LED module, showing still another alternative geometric configuration of the luminescent converter and the reflector.

Fig. 12 is a schematic sectional view of the LED and the reflector in fig. 11.

DETAILED DESCRIPTION

Light emitting diodes, LEDs, are used for a wide variety of applications.

Often, a luminescent converter is integrated into the LED module to create light of a different color than the light originally emitted from the LED.

In order to obtain a pure color of the light emitted from a LED module using luminescent conversion, it is important that no excitation light be allowed to exit from the LED module. This is particularly important in applications where the required color temperature is specified by standards and regulations. To this end, a filter is sometimes disposed in the LED module in order to filter away any remaining excitation light from the LED module output.

Fig. 1 schematically illustrates an exemplary embodiment of a LED module comprising a LED. The LED is fed with electrical current via terminals, and the output light of the LED is coupled out of the LED module via an essentially hemispherical lens. The LED is arranged to emit ultraviolet (UV) light, and a phosphor layer converts the UV light to white light, i.e. to a mixture of red, green, and blue light. Total conversion of the UV light is not achieved as the phosphor layer would then have to be too thick, leading to a high re-absorption of red, green, and blue light. Therefore, in order to reduce the emission of UV light from the module, the lens comprises a reflector, which reflects UV light and transmits visible light. A wavelength selective absorption layer on the surface of the lens significantly reduces any leakage of UV light. The wavelength selectivity of the absorption layer is such that its absorption is higher in the UV wavelength range than in the visible wavelength range. Throughout this disclosure, an absorption layer is defined as a layer consisting of material(s) having an extinction coefficient $k > 0.005$ in the excitation wavelength range. An absorption layer is intended to be located in the light path from the light emitting surface of the LED chip and/or the luminescent converter, to the LED module light output surface; structures such as electrical

wiring, opaque LED chip submounts or the like are not considered absorber layers in this sense.

Fig. 2 shows the LED 12 and the phosphor layer 24 of fig. 1 more in detail. A LED chip 20 is located on a submount 22. Electrical current is fed to the top electrode of the LED chip 20 through a wire 30.

Fig. 3 schematically illustrates an exemplary embodiment of a LED module 110 comprising a LED 112.

Fig. 4 shows the LED 112 of fig. 3 more in detail. A LED chip 120 is flip-chip mounted onto a submount 122. Electrical current is fed to the top electrode of the LED chip 120 through a conductor 130 in a via-hole. The LED chip 120 emits blue excitation light in the wavelength range 400-470 nm, with a peak wavelength of about 450 nm. The excitation light is converted to amber light at about 600 nm by a luminescent phosphor material layer 124 attached to or deposited on the LED chip 120; in this particular example, the phosphor material is a LUMIRAMIC® comprising $(\text{BaSr})_2\text{Si}_5\text{N}_8:\text{Eu}$, i.e. Barium Strontium Silicon Nitride doped with Europium. Its emission wavelength characteristic may be varied by changing the ratio between Barium and Strontium; in this case, 85% Ba and 15% Sr is used. On top of the LUMIRAMIC® layer 124, there is a multi-layer reflector coating 126, which incorporates an absorbing layer. Locating the reflector directly on the LUMIRAMIC® layer has the advantage of reflecting back a larger portion of the unconverted excitation light onto the LUMIRAMIC® layer, and thus increasing the conversion efficiency.

A multi-layer reflector is a type of interference filter that consists of several alternating layers having different indices of refraction; their wavelength response can be designed relatively freely, and they can be designed to give a high suppression of the excitation light. Multi-layer reflectors are therefore very well suited for removing excitation light from the LED module output.

However, as the transparency of a typical interference filter coating varies with the angle of incidence of the light impinging on the interference filter coating, some excitation light will leak through the filter due to the fact that LEDs and wavelength converters typically do not produce a collimated output.

Table 1 gives an example of the structure of a multi-layer reflector that is not provided with an internal absorber layer; its corresponding transmittance as a function of angle of incidence, relative to the reflector surface normal, is given in fig. 5. The filter is made up of alternating layers of SiO_2 , having a refractive index of approx. 1.46, and Nb_2O_5 , with a refractive index of approx. 2.39. Layer no. 1 is adjacent to a LUMIRAMIC®

Layer	Material	d (nm)
1	Nb ₂ O ₅	22.43
2	SiO ₂	47.46
3	Nb ₂ O ₅	58.51
4	SiO ₂	37.19
5	Nb ₂ O ₅	56.08
6	SiO ₂	58.00
7	Nb ₂ O ₅	167.17
8	SiO ₂	61.99
9	Nb ₂ O ₅	163.83
10	SiO ₂	62.79
11	Nb ₂ O ₅	164.02
12	SiO ₂	86.66
13	Nb ₂ O ₅	31.59
14	SiO ₂	86.17
15	Nb ₂ O ₅	38.59
16	SiO ₂	78.94
17	Nb ₂ O ₅	56.06
18	SiO ₂	32.39
19	Nb ₂ O ₅	81.56
20	SiO ₂	39.43
21	Nb ₂ O ₅	179.54
22	SiO ₂	55.61
23	Nb ₂ O ₅	164.17
24	SiO ₂	67.07
25	Nb ₂ O ₅	162.12
26	SiO ₂	60.98
27	Nb ₂ O ₅	74.36
28	SiO ₂	21.77
29	Nb ₂ O ₅	63.28
30	SiO ₂	52.35
31	Nb ₂ O ₅	295.69
32	SiO ₂	51.12
33	Nb ₂ O ₅	159.13
34	SiO ₂	71.99
35	Nb ₂ O ₅	154.03
36	SiO ₂	72.77
37	Nb ₂ O ₅	153.48
38	SiO ₂	63.71
39	Nb ₂ O ₅	146.28
40	SiO ₂	77.15
41	Nb ₂ O ₅	5.71
Total Thickness		3583.18

Table 1.

converter, and layer no. 41 is adjacent to a lens having a refractive index of about 1.5; d signifies the thickness of each layer in nanometers.

Table 2 gives an example of the structure of the multi-layer reflector 126 of the LED module described above with reference to figs 2-3, wherein the filter incorporates an integrated absorber layer of Fe₂O₃. The filter's transmittance as a function of angle of incidence is given in fig. 6. Layer no. 1 is adjacent to the LUMIRAMIC® converter 124 and layer no. 17 is adjacent to the lens 18, which consists of SiO₂. Note that the thickness of the reflection filter is approximately one third of the thickness of the reflection filter of table 1. Also, the absorber layer is an integral part of the reflector and contributes to the reflective properties of the device, since Fe₂O₃ has an index of refraction of 3.11, significantly different from the index of refraction of the adjacent Nb₂O₅ layers. The reflection filter multilayer structure surrounding the thin absorbing Fe₂O₃ layer, on the other hand, enhances the absorption of the thin Fe₂O₃ layer.

Layer	Material	d (nm)
1	Nb ₂ O ₅	149.61
2	SiO ₂	46.59
3	Nb ₂ O ₅	162.56
4	SiO ₂	59.38
5	Nb ₂ O ₅	160.02
6	SiO ₂	62.68
7	Nb ₂ O ₅	78.00
8	Fe₂O₃	8.40
9	Nb ₂ O ₅	80.66
10	SiO ₂	64.37
11	Nb ₂ O ₅	46.08
12	SiO ₂	72.79
13	Nb ₂ O ₅	31.75
14	SiO ₂	95.16
15	Nb ₂ O ₅	44.42
16	SiO ₂	53.56
17	Nb ₂ O ₅	31.17
Total Thickness		1247.19

Table 2

15

The significant difference between the angular dependencies of the two filters of the graphs in figs 5-6 is impressive. By integrating only a thin layer of an absorber into the filter, the filter can not only be made thinner and fabricated using fewer process steps; also

20

the angular dependency of the transmittance of blue light is significantly reduced, and higher-order transmission spikes at low angles are removed.

Fig. 7 schematically illustrates an exemplary embodiment of a LED module 210 comprising a LED 212 and a separate phosphor/reflector/absorber portion 224/226. The configuration of the LED 212 and the phosphor/reflector/absorber portion is illustrated more in detail in fig. 8, which shows a multi-layer reflector 226, comprising a plurality of transparent, alternating reflector layers and a plurality of integrated absorber layers deposited onto a layer of phosphor 224.

Figs 9 and 10 illustrate an alternative geometry of the LED module, wherein the LED chip 320 and the luminescent converter 324 are mounted side by side on a submount 322. Excitation light from the LED chip is reflected onto the luminescent converter 324 by an essentially parabolic multi-layer reflector 326, which also incorporates an absorber layer. The reflector 326 is arranged to transmit the converted light from the luminescent converter, and the absorption layer reduces the reflector's 326 transmission of any excitation light impinging on the reflector 326 at substantially oblique angles.

The geometric separation of the LED chip 320 and the luminescent converter 324 also makes it possible to locate and extend a separate hemispherical absorber (not shown) around the luminescent converter, such that converted light from the luminescent converter will pass through the separate absorber at a normal angle of incidence, and excitation light leaking through the reflector will pass through the separate absorber at an oblique angle. This will make the path through the absorber longer for the excitation light than for the converted light.

Figs 11 and 12 show an embodiment illustrating how a geometric separation of the LED chip from the luminescent converter may enable different absorption levels of excitation light and converted light, respectively, and thereby contribute to improving the colour temperature of a LED module. A wavelength selective reflector 426 reflects the light from a LED chip 420 onto a luminescent converter 424. Converted light from the luminescent converter passes through the reflector, and then through an absorber 428 at a normal angle of incidence. Any excitation light from the LED chip 420 that may leak through the wavelength selective reflector 426 will pass through the absorber 428 at an oblique angle. This will make the path through the absorber 428 longer for the excitation light than for the converted light.

In summary, the invention relates to a LED module which converts pump light from a LED chip to light at another wavelength, which is emitted from the module. The conversion takes place in a portion of a luminescent material. The color purity of the LED module is enhanced by reducing any leakage of pump light using a reflector in combination with an absorber. In one embodiment, the absorber is integrated as one or several thin absorbing layers between the layers of a multi-layer interference filter; this may yield an even higher reduction of pump light leakage from the module.

The person skilled in the art realizes that the present invention by no means is limited to the preferred embodiments described above. On the contrary, many modifications and variations are possible within the scope of the appended claims. For example, the invention is not limited to absorption layers of Fe_2O_3 ; also other materials featuring an absorption in the excitation wavelength range may be used, for example but not limited to zinc iron oxide, titanium iron oxide, vanadium oxide, bismuth oxide, copper oxide, bismuth vanadate, zirconium praseodymium silicate, or any mixture thereof.

Neither is the invention limited to luminescent layers of LUMIRAMIC® or other phosphorescent materials; any atomic or molecular species or solid-state compounds that convert at least a part of incident electromagnetic radiation to electromagnetic radiation with a characteristic signature may be used, such as fluorescent dyes or luminescent quantum dots.

In the examples above, the multi-layer reflectors comprise alternating layers of Nb_2O_5 and SiO_2 . Other combinations of two or more different materials, having different indices of refraction, may be used and are covered by the appended claims. Further, the reflector is not limited to multi-layer reflectors; any type of wavelength selective reflector capable of reflecting the excitation wavelength while at the same time transmitting the converted wavelength may be used. The absorber may consist of one or several absorbing layers integrated in the reflector, or it may be a separate absorber located elsewhere in the LED module. Even though the entire LED module preferably is comprised in a single housing, it may also be divided between separate housings. Different parts of the device may be separated between different modules, which, when cooperating, obtain the same function as claimed. Further, even though in the examples above, blue or UV light is used to generate amber or white light, other combinations are also covered by the appended claims. The invention is not limited to LED chips or luminescent converters emitting visible light; they may as well emit in the IR and UV regions. Nor is the invention limited to LED:s emitting excitation light in a broadband optical spectrum. Also narrow-band LED:s incorporating any

type of optical feed-back and stimulated emission, such as diode lasers, are within the scope of the claim. Features disclosed in separate embodiments in the description above may be advantageously combined.

5 The use of the indefinite article "a" or "an" in this disclosure does not exclude a plurality. Any reference signs in the claims should not be construed as limiting the scope.

CLAIMS:

1. A lightsource, comprising a LED chip(20, 120, 220, 320, 420) adapted for emitting excitation light in a first wavelength range; a wavelength converter (24, 124, 224, 324, 424), adapted for converting excitation light to converted light in a second wavelength range; and a reflector (26, 126, 226, 326, 426), adapted for transmitting converted light, and
5 for reflecting excitation light onto the wavelength converter (24, 124, 224, 324, 424); the lightsource (10, 110, 210, 310, 410) being **characterized** in comprising an absorption layer (28, 428), arranged for absorbing unconverted excitation light.
2. The lightsource according to claim 1, wherein the reflector (124, 224, 324) is a
10 multi-layer reflector comprising a plurality of alternating layers of at least two different materials having at least two different indices of refraction.
3. The lightsource according to claim 2, wherein the absorption layer is located
15 between layers of the reflector (124, 224, 324).
4. The lightsource according to any of the previous claims, wherein the wavelength converter (24, 124, 224) is located between the reflector (26, 126, 226) and the LED chip (20, 120, 220).
- 20 5. The lightsource according to claim 4, wherein the reflector (126), the absorption layer, the wavelength converter (124) and the LED chip (120) are joined to form a single stack (112).

1/6

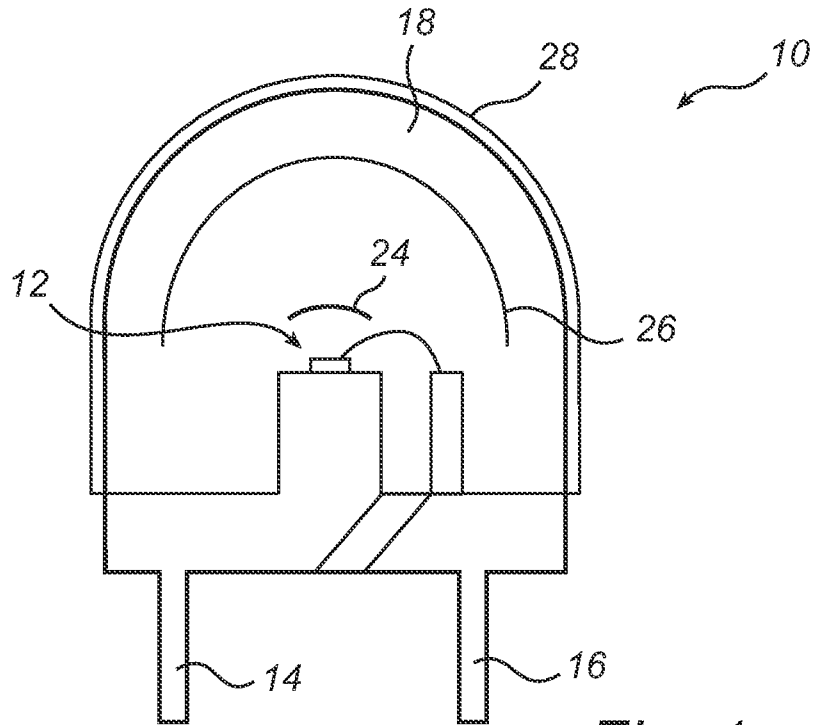


Fig. 1

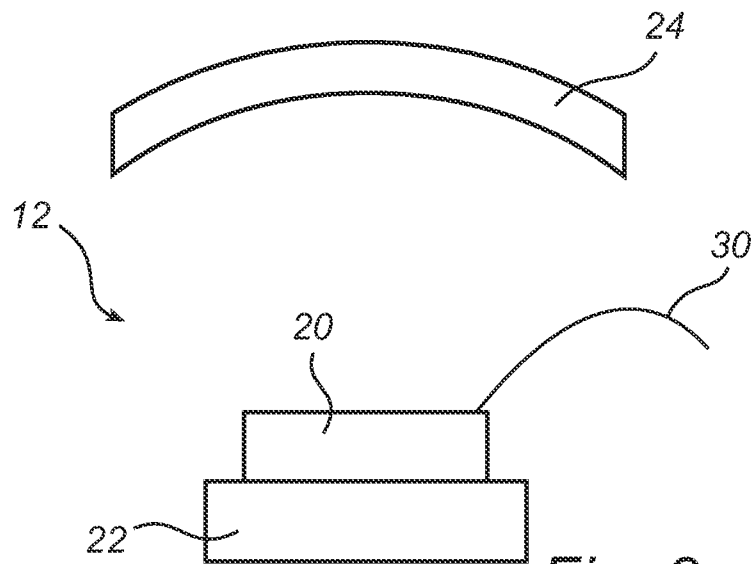


Fig. 2

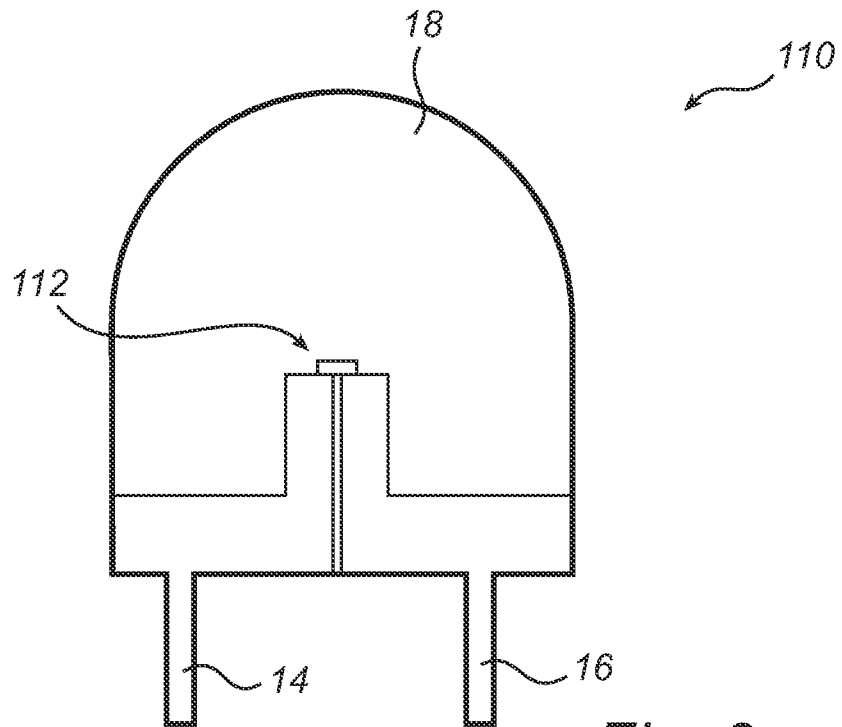


Fig. 3

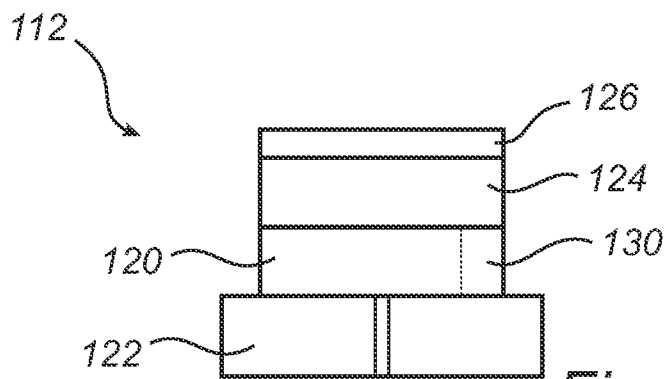


Fig. 4

3/6

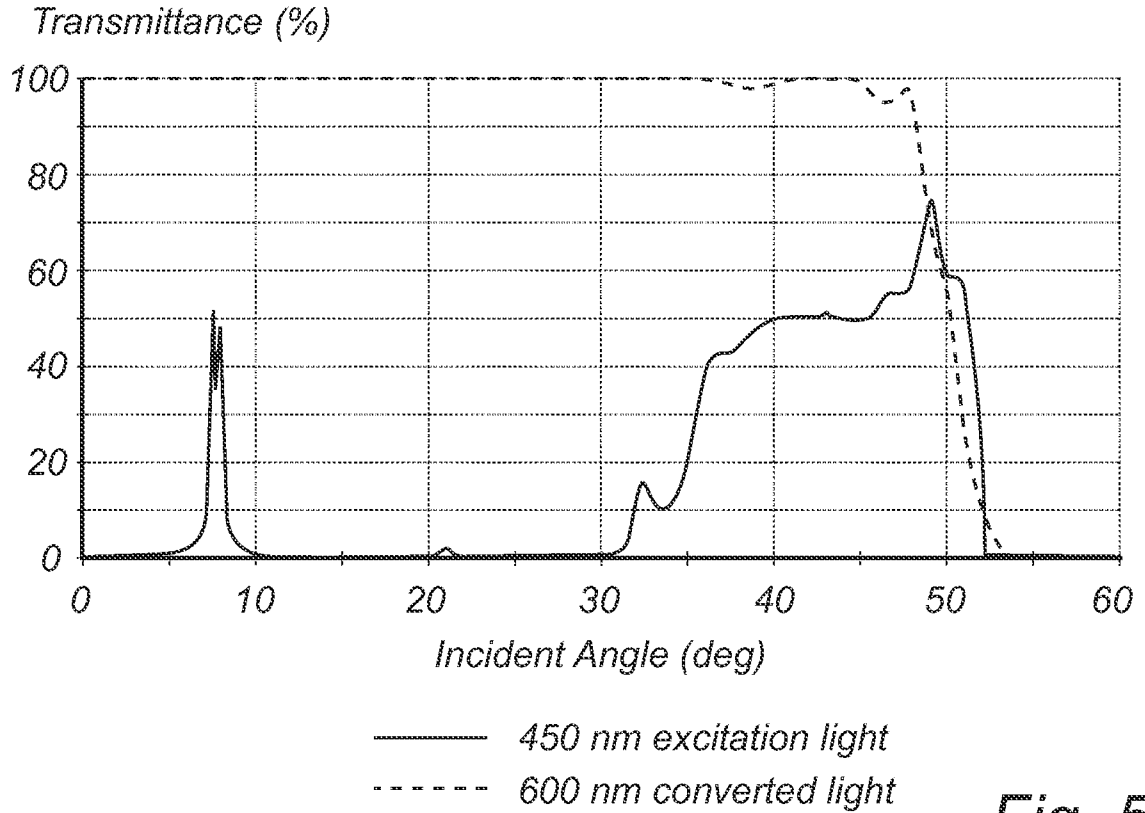


Fig. 5

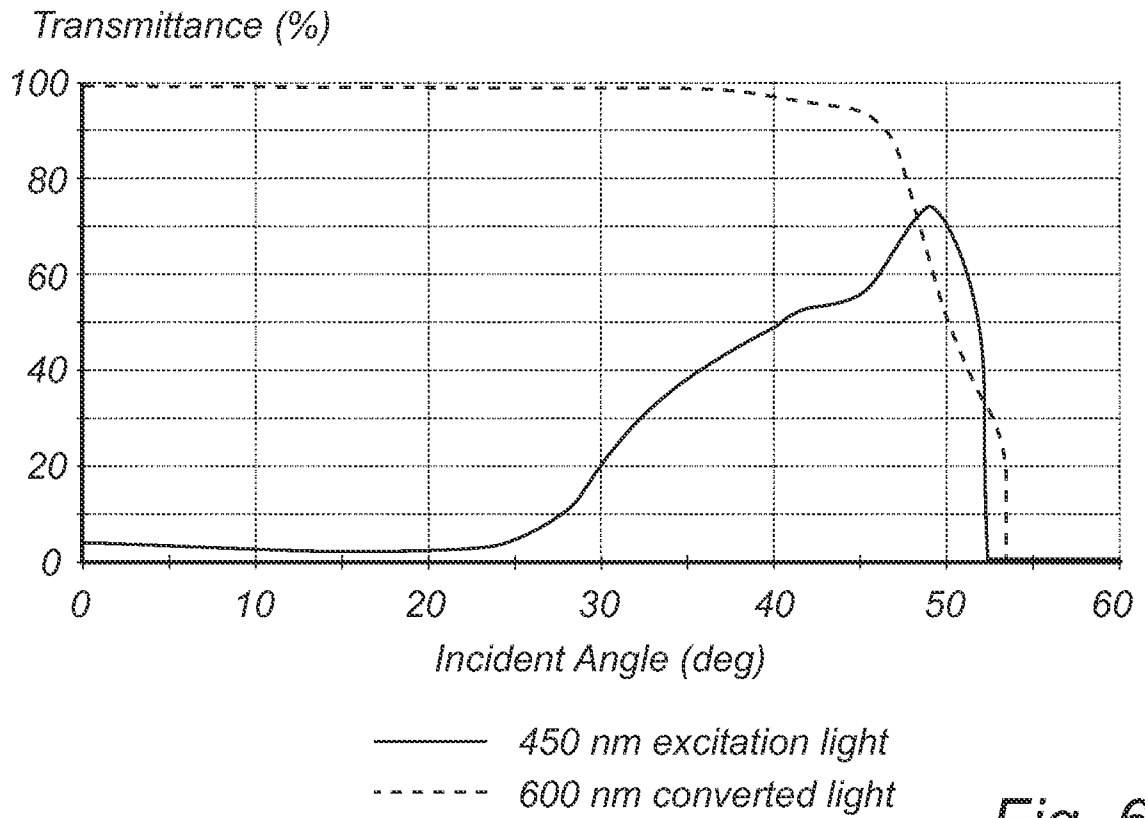


Fig. 6

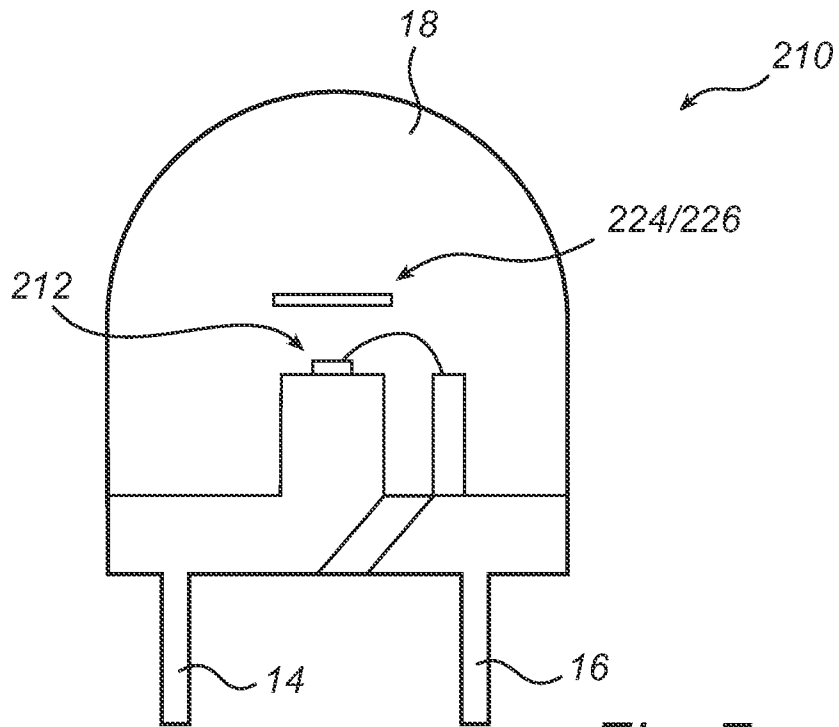


Fig. 7

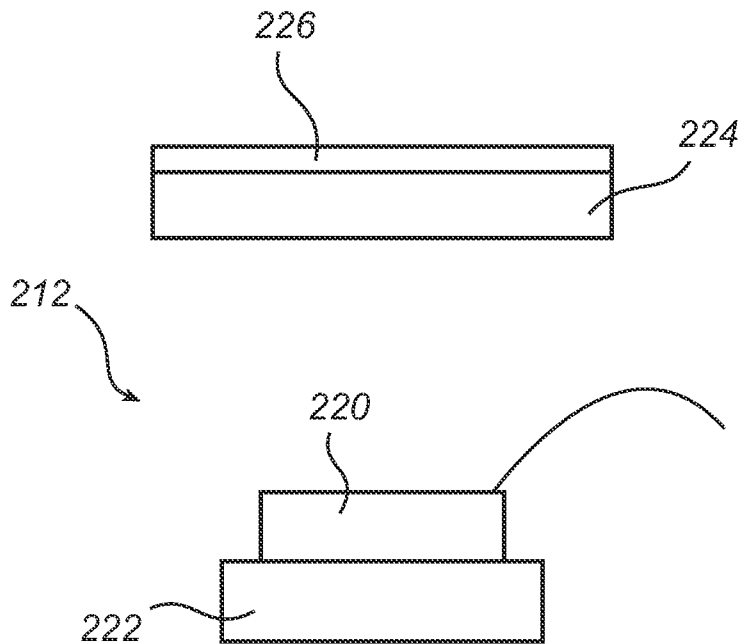


Fig. 8

5/6

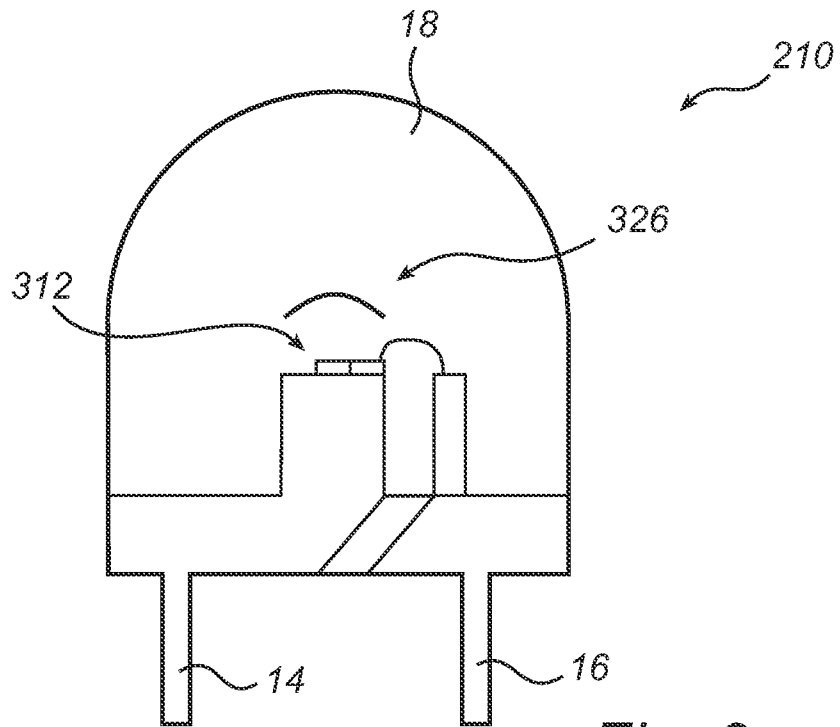


Fig. 9

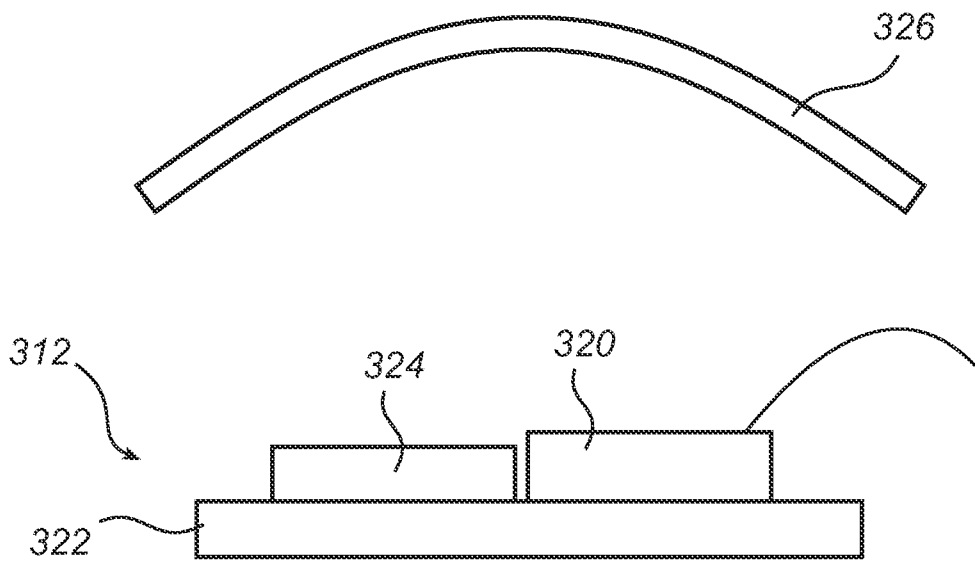


Fig. 10

6/6

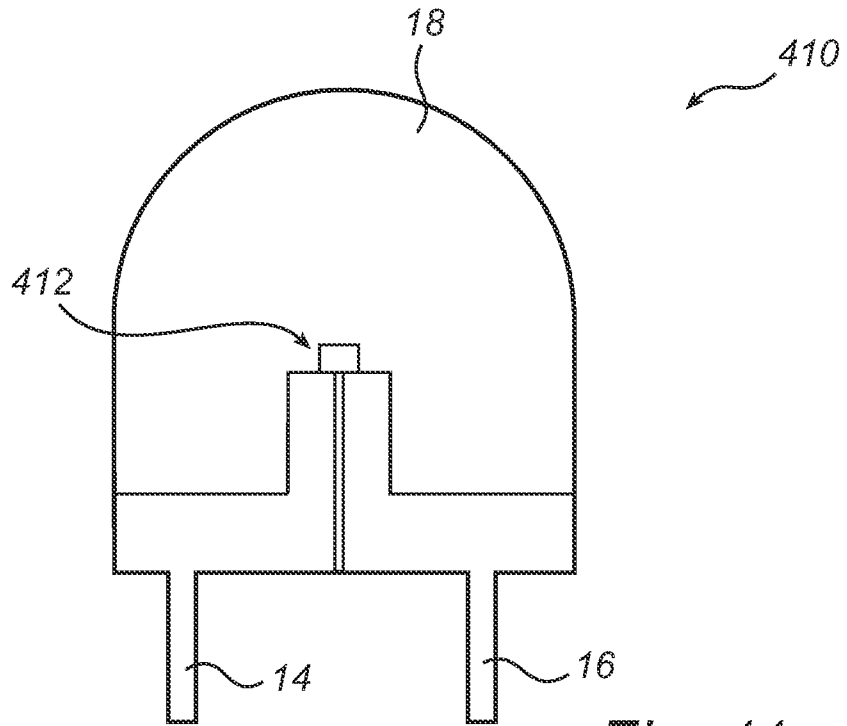


Fig. 11

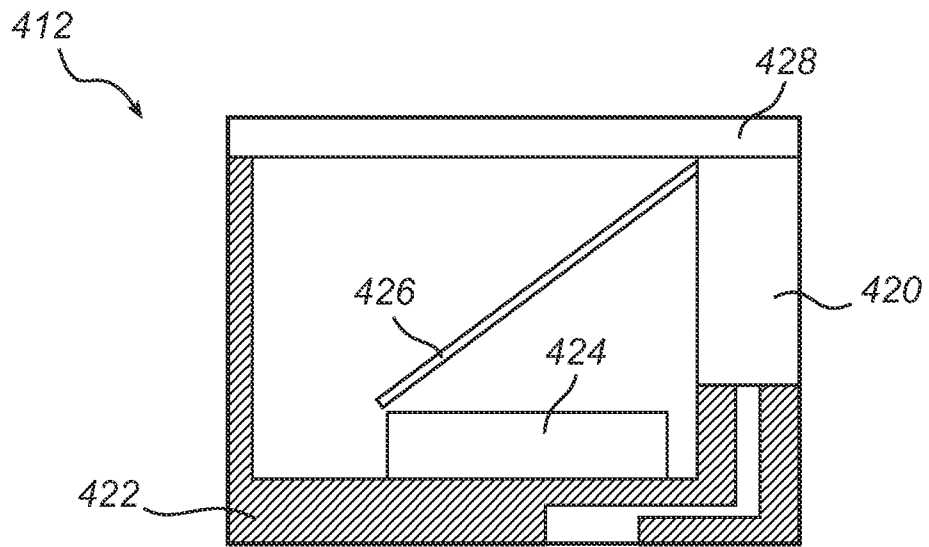


Fig. 12

INTERNATIONAL SEARCH REPORT

International application No
PCT/IB2009/052264

A. CLASSIFICATION OF SUBJECT MATTER
INV. H01L33/00

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)
H01L G05B

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practical, search terms used)

EPO-Internal, WPI Data

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	US 2007/023762 A1 (GUMINS SAMUEL P [US] ET AL) 1 February 2007 (2007-02-01) paragraph [0037] - paragraph [0061]; figures 1-9	1-5
X	EP 1 916 719 A (3M INNOVATIVE PROPERTIES CO [US]) 30 April 2008 (2008-04-30) paragraph [0019] - paragraph [0077]; figures 1-15	1,2,4
A	EP 1 403 934 A (LUMILEDS LIGHTING LLC [US]) 31 March 2004 (2004-03-31) paragraph [0008] - paragraph [0025]; figures 1-7	3,5
A		1-5
	-/--	

Further documents are listed in the continuation of Box C.

See patent family annex.

* Special categories of cited documents:

- *A* document defining the general state of the art which is not considered to be of particular relevance
- *E* earlier document but published on or after the international filing date
- *L* document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)
- *O* document referring to an oral disclosure, use, exhibition or other means
- *P* document published prior to the international filing date but later than the priority date claimed

- *T* later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention
- *X* document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone
- *Y* document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art.
- * & * document member of the same patent family

Date of the actual completion of the international search

15 September 2009

Date of mailing of the international search report

23/09/2009

Name and mailing address of the ISA/

European Patent Office, P.B. 5818 Patentlaan 2
NL - 2280 HV Rijswijk
Tel. (+31-70) 340-2040,
Fax: (+31-70) 340-3016

Authorized officer

Krause, Joachim

INTERNATIONAL SEARCH REPORT

International application No
PCT/IB2009/052264

C(Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	WO 2007/039849 A (PHILIPS INTELLECTUAL PROPERTY [DE]; KONINKL PHILIPS ELECTRONICS NV [NL] 12 April 2007 (2007-04-12) page 6, line 8 - page 11, line 11; figures 1-7 -----	1-5
A	EP 1 187 226 A (CITIZEN ELECTRONICS [JP]) 13 March 2002 (2002-03-13) paragraph [0023] - paragraph [0048]; figures 2-23 -----	1-5
A	GB 2 215 075 A (BRITISH TELECOMM [GB]) 13 September 1989 (1989-09-13) page 4, last paragraph - page 11, paragraph 3; figures 1-7 -----	1-5

INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No

PCT/IB2009/052264

Patent document cited in search report	Publication date	Patent family member(s)	Publication date
US 2007023762 A1	01-02-2007	WO 2007017122 A1	15-02-2007
EP 1916719 A	30-04-2008	NONE	
EP 1403934 A	31-03-2004	JP 2004119984 A	15-04-2004
		US 2004061124 A1	01-04-2004
		US 2004217383 A1	04-11-2004
WO 2007039849 A	12-04-2007	CN 101283457 A	08-10-2008
		JP 2009512130 T	19-03-2009
		KR 20080064854 A	09-07-2008
		US 2008265749 A1	30-10-2008
EP 1187226 A	13-03-2002	NONE	
GB 2215075 A	13-09-1989	NONE	